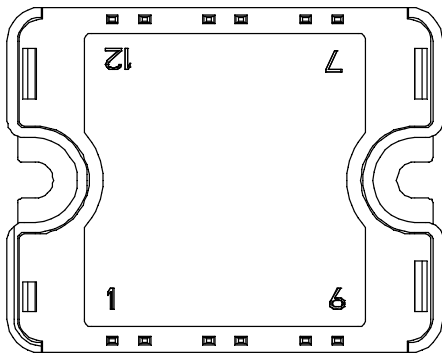
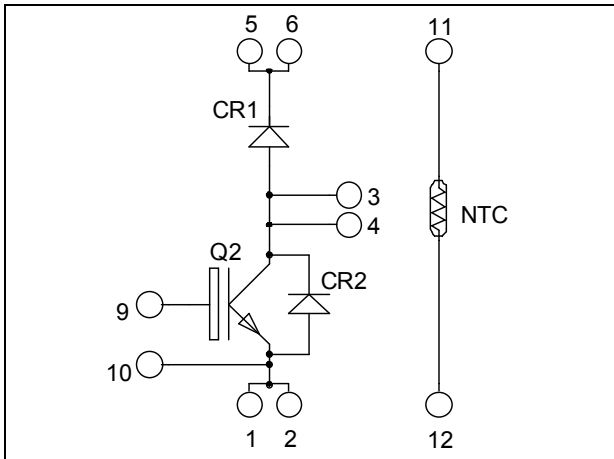


## Boost chopper NPT IGBT Power Module

**$V_{CES} = 600V$**   
 **$I_C = 90A @ T_c = 80^\circ C$**



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings         | Unit        |
|-----------|---------------------------------------|---------------------|-------------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 600                 | V           |
| $I_C$     | Continuous Collector Current          | $T_c = 25^\circ C$  | 110         |
|           |                                       | $T_c = 80^\circ C$  | 90          |
| $I_{CM}$  | Pulsed Collector Current              | $T_c = 25^\circ C$  | 315         |
| $V_{GE}$  | Gate - Emitter Voltage                | $\pm 20$            | V           |
| $P_D$     | Maximum Power Dissipation             | $T_c = 25^\circ C$  | 416         |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 150^\circ C$ | 200A @ 600V |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                                | Min                       | Typ | Max       | Unit          |
|---------------|--------------------------------------|--|---------------------------|-----|-----------|---------------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0\text{V}$<br>$V_{CE} = 600\text{V}$ | $T_j = 25^\circ\text{C}$  |     | 250       | $\mu\text{A}$ |
|               |                                      |  | $T_j = 125^\circ\text{C}$ |     | 500       |               |
| $V_{CE(sat)}$ | Collector Emitter saturation Voltage | $V_{GE} = 15\text{V}$<br>$I_C = 90\text{A}$    | $T_j = 25^\circ\text{C}$  | 2.0 | 2.5       | V             |
|               |                                      |  | $T_j = 125^\circ\text{C}$ | 2.2 |           |               |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 1\text{mA}$            | 3                         |     | 5         | V             |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$      |                           |     | $\pm 150$ | nA            |

**Dynamic Characteristics**

| Symbol       | Characteristic               | Test Conditions  | Min                       | Typ  | Max | Unit |
|--------------|------------------------------|--|---------------------------|------|-----|------|
| $C_{ies}$    | Input Capacitance            | $V_{GE} = 0\text{V}$<br>$V_{CE} = 25\text{V}$<br>$f = 1\text{MHz}$   |                           | 4300 |     | pF   |
| $C_{oes}$    | Output Capacitance           |  |                           | 470  |     |      |
| $C_{res}$    | Reverse Transfer Capacitance |  |                           | 400  |     |      |
| $Q_g$        | Total gate Charge            | $V_{GE} = 15\text{V}$<br>$V_{Bus} = 300\text{V}$<br>$I_C = 90\text{A}$   |                           | 330  |     | nC   |
| $Q_{ge}$     | Gate – Emitter Charge        |  |                           | 290  |     |      |
| $Q_{gc}$     | Gate – Collector Charge      |  |                           | 200  |     |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $25^\circ\text{C}$ )<br>$V_{GE} = 15\text{V}$<br>$V_{Bus} = 400\text{V}$<br>$I_C = 90\text{A}$<br>$R_G = 5\ \Omega$  |                           | 26   |     | ns   |
| $T_r$        | Rise Time                    |  |                           | 25   |     |      |
| $T_{d(off)}$ | Turn-off Delay Time          |  |                           | 150  |     |      |
| $T_f$        | Fall Time                    |  |                           | 30   |     |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $125^\circ\text{C}$ )<br>$V_{GE} = 15\text{V}$<br>$V_{Bus} = 400\text{V}$<br>$I_C = 90\text{A}$<br>$R_G = 5\ \Omega$ |                           | 26   |     | ns   |
| $T_r$        | Rise Time                    |  |                           | 25   |     |      |
| $T_{d(off)}$ | Turn-off Delay Time          |  |                           | 170  |     |      |
| $T_f$        | Fall Time                    |  |                           | 40   |     |      |
| $E_{on}$     | Turn-on Switching Energy     | $V_{GE} = 15\text{V}$<br>$V_{Bus} = 400\text{V}$<br>$I_C = 90\text{A}$<br>$R_G = 5\ \Omega$  | $T_j = 125^\circ\text{C}$ | 4.3  |     | mJ   |
| $E_{off}$    | Turn-off Switching Energy    |  | $T_j = 125^\circ\text{C}$ | 3.5  |     |      |

**Chopper diode ratings and characteristics**

| Symbol    | Characteristic                          | Test Conditions   | Min                       | Typ  | Max | Unit          |
|-----------|---|---|---------------------------|------|-----|---------------|
| $V_{RRM}$ | Maximum Peak Repetitive Reverse Voltage |   | 600                       |      |     | V             |
| $I_{RM}$  | Maximum Reverse Leakage Current         | $V_R = 600\text{V}$   | $T_j = 25^\circ\text{C}$  |      | 100 | $\mu\text{A}$ |
|           |   |   | $T_j = 125^\circ\text{C}$ |      | 500 |               |
| $I_F$     | DC Forward Current                      | $T_c = 80^\circ\text{C}$  |                           | 100  |     | A             |
| $V_F$     | Diode Forward Voltage                   | $I_F = 100\text{A}$   |                           | 1.6  | 2   | V             |
|           |   | $I_F = 200\text{A}$   |                           | 2    |     |               |
|           |   | $I_F = 100\text{A}$   | $T_j = 125^\circ\text{C}$ | 1.3  |     |               |
| $t_{rr}$  | Reverse Recovery Time                   | $I_F = 100\text{A}$<br>$V_R = 400\text{V}$<br>$di/dt = 200\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$  | 160  |     | ns            |
|           |   |   | $T_j = 125^\circ\text{C}$ | 220  |     |               |
| $Q_{rr}$  | Reverse Recovery Charge                 | $I_F = 100\text{A}$<br>$V_R = 400\text{V}$<br>$di/dt = 200\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$  | 290  |     | nC            |
|           |   |   | $T_j = 125^\circ\text{C}$ | 1530 |     |               |

## Thermal and package characteristics

| Symbol            | Characteristic   | Min         | Typ | Max  | Unit |     |
|-------------------|--|-------------|-----|------|------|-----|
| R <sub>thJC</sub> | Junction to Case Thermal Resistance                                      | IGBT        |     | 0.3  | °C/W |     |
|                   |  | Diode       |     | 0.55 |      |     |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz | 2500        |     |      | V    |     |
| T <sub>J</sub>    | Operating junction temperature range                                     | -40         |     | 150  | °C   |     |
| T <sub>STG</sub>  | Storage Temperature Range  | -40         |     | 125  |      |     |
| T <sub>C</sub>    | Operating Case Temperature   | -40         |     | 100  |      |     |
| Torque            | Mounting torque  | To heatsink | M4  | 2.5  | 4.7  | N.m |
| Wt                | Package Weight   |             |     |      | 80   | g   |

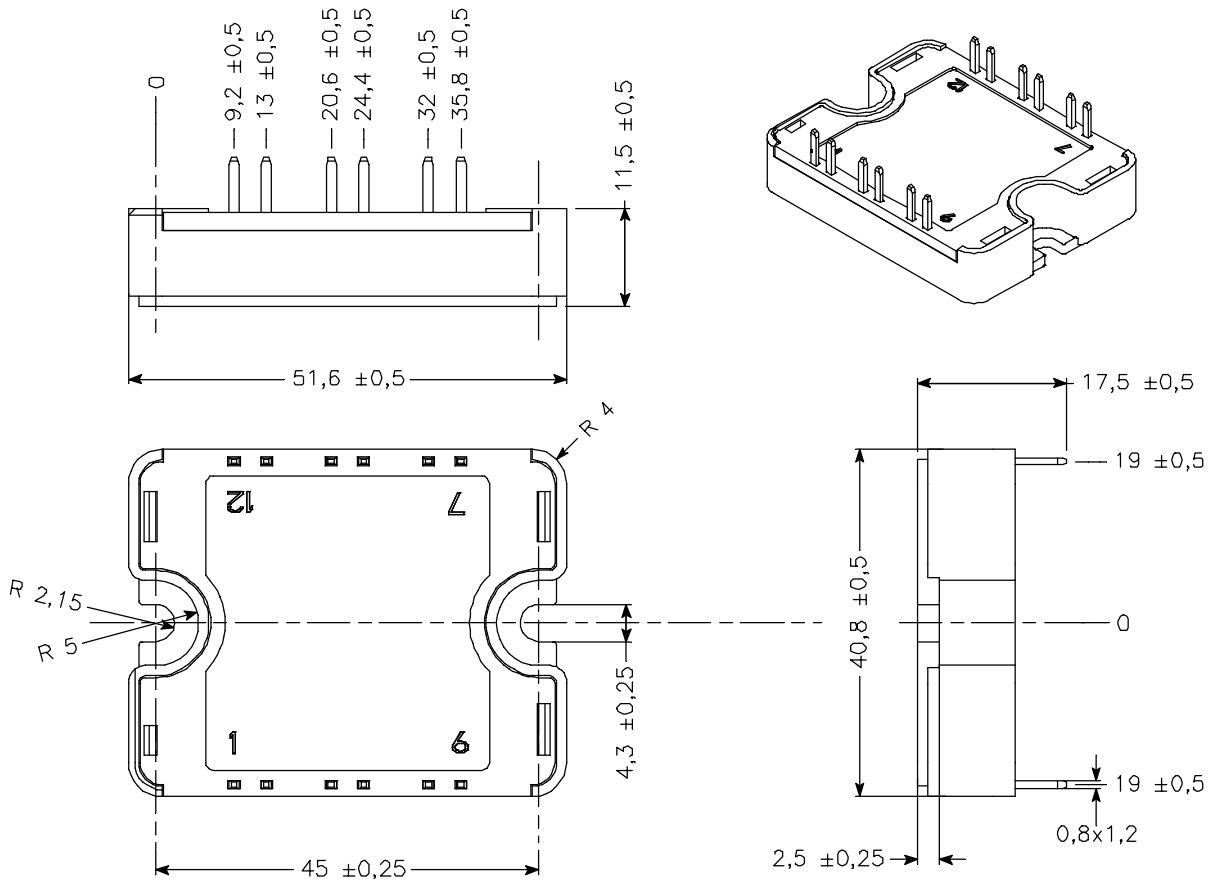
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol             | Characteristic             | Min | Typ  | Max | Unit |
|--------------------|----------------------------|-----|------|-----|------|
| R <sub>25</sub>    | Resistance @ 25°C          |     | 50   |     | kΩ   |
| B <sub>25/85</sub> | T <sub>25</sub> = 298.15 K |     | 3952 |     | K    |

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

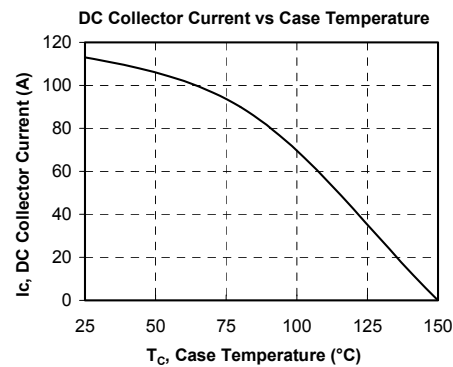
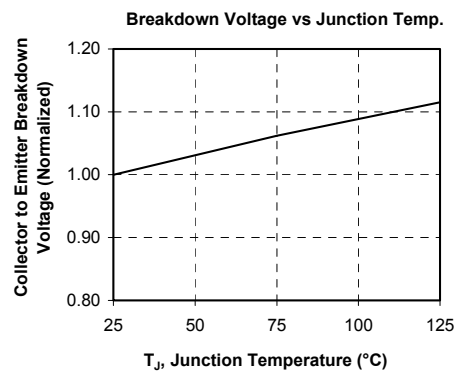
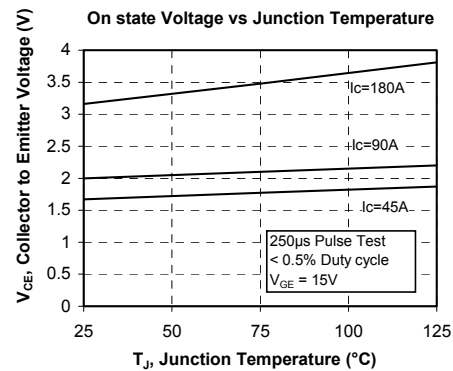
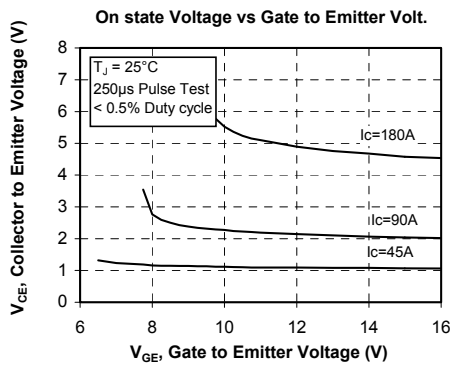
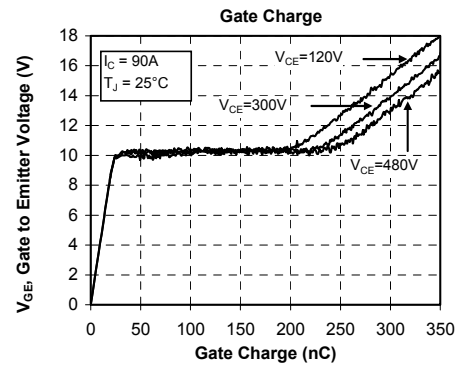
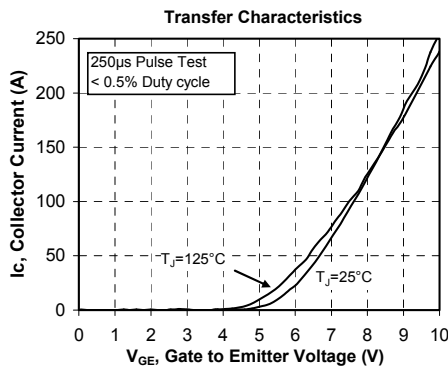
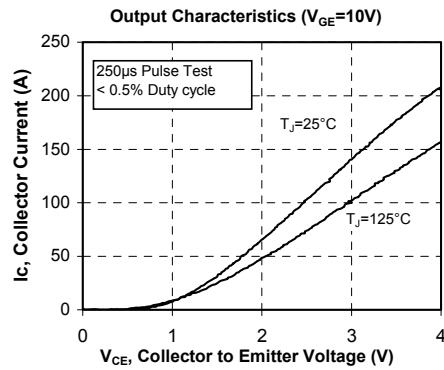
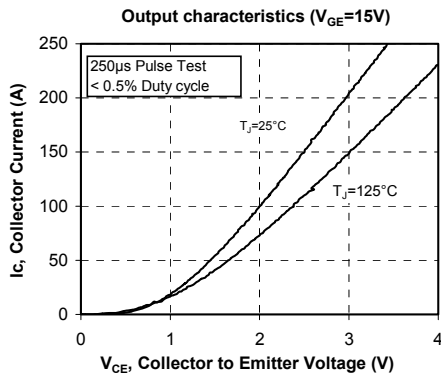
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

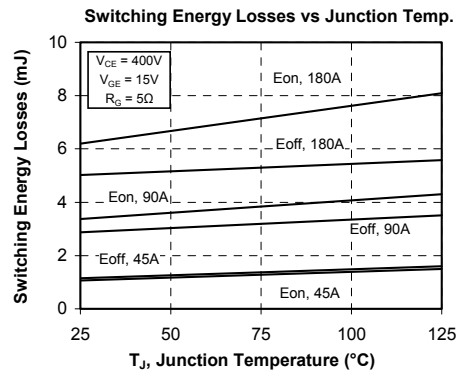
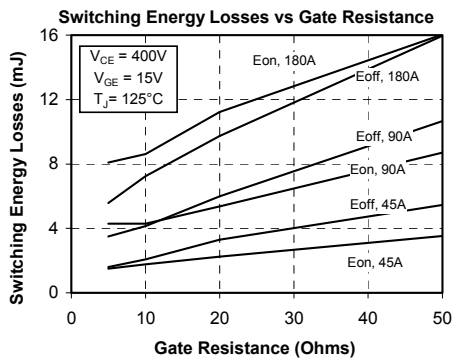
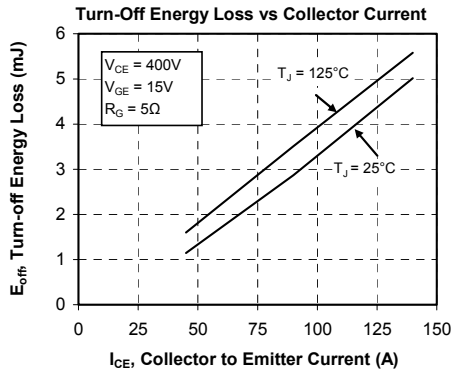
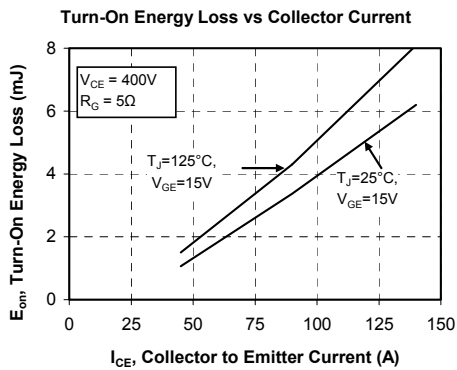
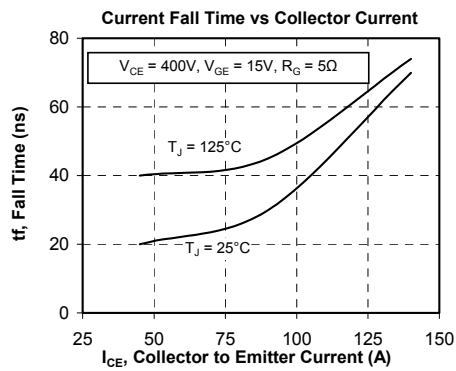
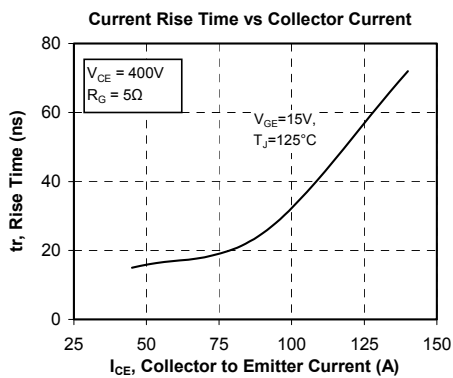
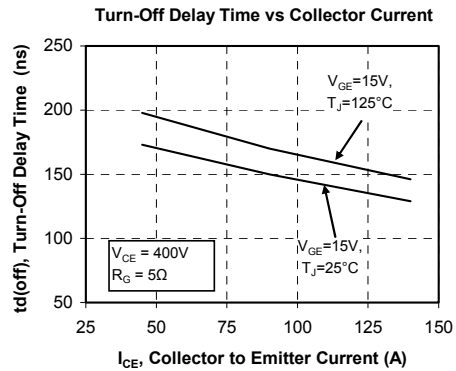
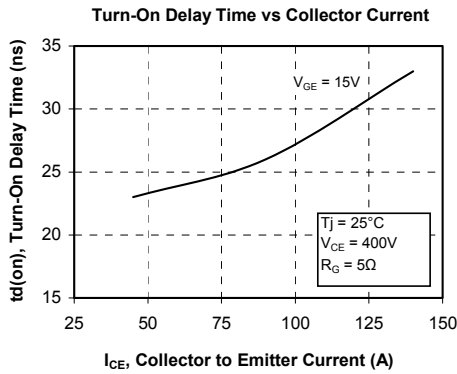
## SP1 Package outline (dimensions in mm)

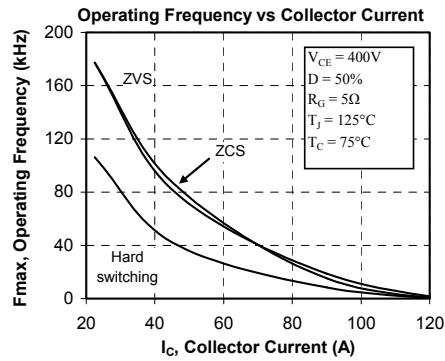
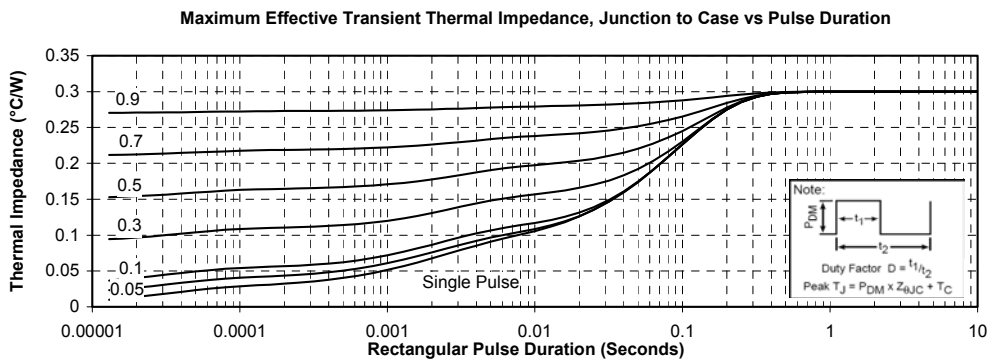
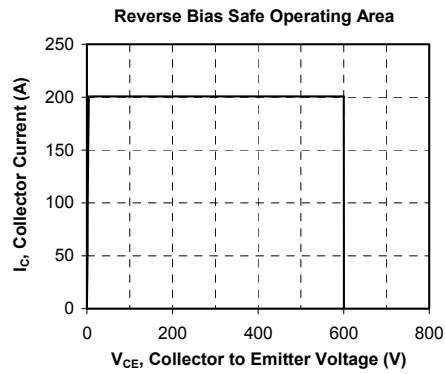
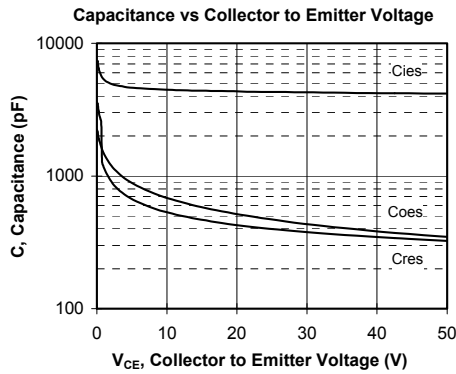


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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